WHAT IS CLAIMED IS:

1. A layered structure of wire(s) provided in a contact hole formed in an insulating film in which a first insulating layer and a second insulating layer made of different material from each other are stacked in this order, wherein the layered structure of wire(s) including:

a first metal layer which is made of a refractory metal;

a wiring layer, formed on said first metal layer, which is made of a metal whose resistance is lower than that of the refractory metal; and

a second metal layer, formed on said wiring layer, which is made of a refractory metal and is so formed as to be thicker than said first insulating layer.

2. A layered structure of wire(s) according to Claim 1, wherein the contact hole is formed in such a manner that said second insulating layer has a taper slower than that of said first insulating layer.

3. A layered structure of wire(s) according to Claim 1, wherein said second insulating layer is formed such that the thickness of said second insulating layer is greater than or equal to that of said first insulating layer and is less than or equal to approximately 600 nm.

4. A layered structure of wire(s) according to Claim 1, wherein said first metal layer is formed thicker than said first insulating layer.

5. A layered structure of wire(s) provided in a contact hole formed in an insulating film in which a first insulating layer and a second insulating layer made of different material from each other are stacked in this order, wherein the layered structure of wire(s) including:

a first metal layer which is made of a refractory metal;

a wiring layer, formed on said first metal layer, which is made of a metal whose resistance is lower than that of the refractory metal; and

a second metal layer, formed on said wiring layer, which is made of a refractory metal and is so formed as to be thicker than a distance between an overhang and said first insulating layer therebelow,

wherein said contact hole is formed by using a predetermined etchant, and in said second insulating film there is formed the overhang which is protruded beyond said first insulating film toward the center of said contact hole.

6. A layered structure of wire(s) according to Claim 5, wherein said contact hole is formed in such a manner that

said second insulating layer has a taper slower than that of said first insulating layer.

7. A layered structure of wire(s) according to Claim 5, wherein said second insulating layer is formed such that the thickness of said second insulating layer is greater than or equal to that of said first insulating layer and is less than or equal to approximately 600 nm.

8. A layered structure of wire(s) according to Claim 5, wherein said first metal layer is formed thicker than said first insulating layer.

9. A layered structure of wire(s) provided in a contact hole formed in an insulating film in which a first insulating layer and a second insulating layer made of different material from each other are stacked in this order, the layered structure of wire(s) including:

a first metal layer which is made of a refractory metal;

a wiring layer, formed on said first metal layer, which is made of a metal whose resistance is lower than that of the refractory metal; and

a second metal layer, formed on said wiring layer, which is made of a refractory metal and is formed to have thickness such that any severance does not occur due to a

level difference caused by different etching rates of said first insulating layer and said second insulating layer when using a predetermined etchant,

wherein said contact hole is formed by using said predetermined etchant.

10. A layered structure of wire(s) according to Claim 9, wherein said contact hole is formed in such a manner that said second insulating layer has a taper slower than that of said first insulating layer.

11. A layered structure of wire(s) according to Claim 9, wherein said second insulating layer is formed such that the thickness of said second insulating layer is greater than or equal to that of said first insulating layer and is less than or equal to approximately 600 nm.

12. A layered structure of wire(s) according to Claim 9, wherein said first metal layer is formed thicker than said first insulating layer.

13. A method of manufacturing a layered structure of wire(s), the method comprising:

forming a contact hole in an insulating film in which a first insulating layer and a second insulating layer made of different material from each other are stacked in this

order, by etching using a predetermined etchant;

forming a first metal layer which is made of a refractory metal, in the contact hole;

forming a wiring layer, on said first metal layer, which is made of a metal whose resistance is lower than that of the refractory metal; and

forming a second metal layer made of a refractory metal, on said wiring layer, so as to be thicker than said first insulating layer.

14. A method of manufacturing a layered structure of wire(s) according to Claim 13, wherein said forming the contact hole is such that the etching is performed by using an etchant whose etching rate for said first insulating layer is higher than that for the second insulating layer.

15. A display apparatus, including:

a layered structure of wire(s); and

an optical element, formed on said layered structure of wire(s), which has at least an anode, a luminous element layer and a cathode,

wherein said layered structure of wire(s) is provided in a contact hole formed in an insulating film in which a first insulating layer and a second insulating layer made of different material from each other are stacked in this order, and said contact hole is formed by using a predetermined

etchnat, and wherein said layered structure of wire(s) includes:

a first metal layer which is made of a refractory metal;

a wiring layer, formed on said first metal layer, which is made of a metal whose resistance is lower than that of the refractory metal; and

a second metal layer, formed on said wiring layer, which is made of a refractory metal and is formed to have thickness such that any severance does not occur due to a level difference caused by different etching rates of said first insulating layer and said second insulating layer when using a predetermined etchant.

16. A display apparatus according to Claim 15, wherein said contact hole is formed in such a manner that said second insulating layer has a taper slower than that of said first insulating layer.

17. A display apparatus according to Claim 15, wherein said second insulating layer is formed such that the thickness of said second insulating layer is greater than or equal to that of said first insulating layer and is less than or equal to approximately 600 nm.

18. A display apparatus according to Claim 15, wherein said

first metal layer is formed thicker than said first insulating layer.